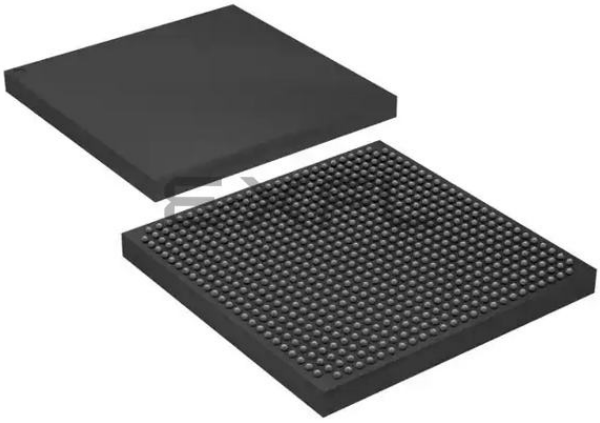

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1248
Number of Logic Elements/Cells	9984
Total RAM Bits	98304
Number of I/O	470
Number of Gates	513000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k200sfi672-2

Table 4. FLEX 10KE Package Sizes

Device	144-Pin TQFP	208-Pin PQFP	240-Pin PQFP RQFP	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	599-Pin PGA	600-Pin BGA	672-Pin FineLine BGA
Pitch (mm)	0.50	0.50	0.50	1.0	1.27	1.0	–	1.27	1.0
Area (mm^2)	484	936	1,197	289	1,225	529	3,904	2,025	729
Length × width (mm × mm)	22 × 22	30.6 × 30.6	34.6 × 34.6	17 × 17	35 × 35	23 × 23	62.5 × 62.5	45 × 45	27 × 27

General Description

Altera FLEX 10KE devices are enhanced versions of FLEX 10K devices. Based on reconfigurable CMOS SRAM elements, the FLEX architecture incorporates all features necessary to implement common gate array megafunctions. With up to 200,000 typical gates, FLEX 10KE devices provide the density, speed, and features to integrate entire systems, including multiple 32-bit buses, into a single device.

The ability to reconfigure FLEX 10KE devices enables 100% testing prior to shipment and allows the designer to focus on simulation and design verification. FLEX 10KE reconfigurability eliminates inventory management for gate array designs and generation of test vectors for fault coverage.

Table 5 shows FLEX 10KE performance for some common designs. All performance values were obtained with Synopsys DesignWare or LPM functions. Special design techniques are not required to implement the applications; the designer simply infers or instantiates a function in a Verilog HDL, VHDL, Altera Hardware Description Language (AHDL), or schematic design file.

Similar to the FLEX 10KE architecture, embedded gate arrays are the fastest-growing segment of the gate array market. As with standard gate arrays, embedded gate arrays implement general logic in a conventional "sea-of-gates" architecture. Additionally, embedded gate arrays have dedicated die areas for implementing large, specialized functions. By embedding functions in silicon, embedded gate arrays reduce die area and increase speed when compared to standard gate arrays. While embedded megafunctions typically cannot be customized, FLEX 10KE devices are programmable, providing the designer with full control over embedded megafunctions and general logic, while facilitating iterative design changes during debugging.

Each FLEX 10KE device contains an embedded array and a logic array. The embedded array is used to implement a variety of memory functions or complex logic functions, such as digital signal processing (DSP), wide data-path manipulation, microcontroller applications, and data-transformation functions. The logic array performs the same function as the sea-of-gates in the gate array and is used to implement general logic such as counters, adders, state machines, and multiplexers. The combination of embedded and logic arrays provides the high performance and high density of embedded gate arrays, enabling designers to implement an entire system on a single device.

FLEX 10KE devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers the EPC1, EPC2, and EPC16 configuration devices, which configure FLEX 10KE devices via a serial data stream. Configuration data can also be downloaded from system RAM or via the Altera BitBlaster™, ByteBlasterMV™, or MasterBlaster download cables. After a FLEX 10KE device has been configured, it can be reconfigured in-circuit by resetting the device and loading new data. Because reconfiguration requires less than 85 ms, real-time changes can be made during system operation.

FLEX 10KE devices contain an interface that permits microprocessors to configure FLEX 10KE devices serially or in-parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat a FLEX 10KE device as memory and configure it by writing to a virtual memory location, making it easy to reconfigure the device.

Functional Description

Each FLEX 10KE device contains an enhanced embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 4,096 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

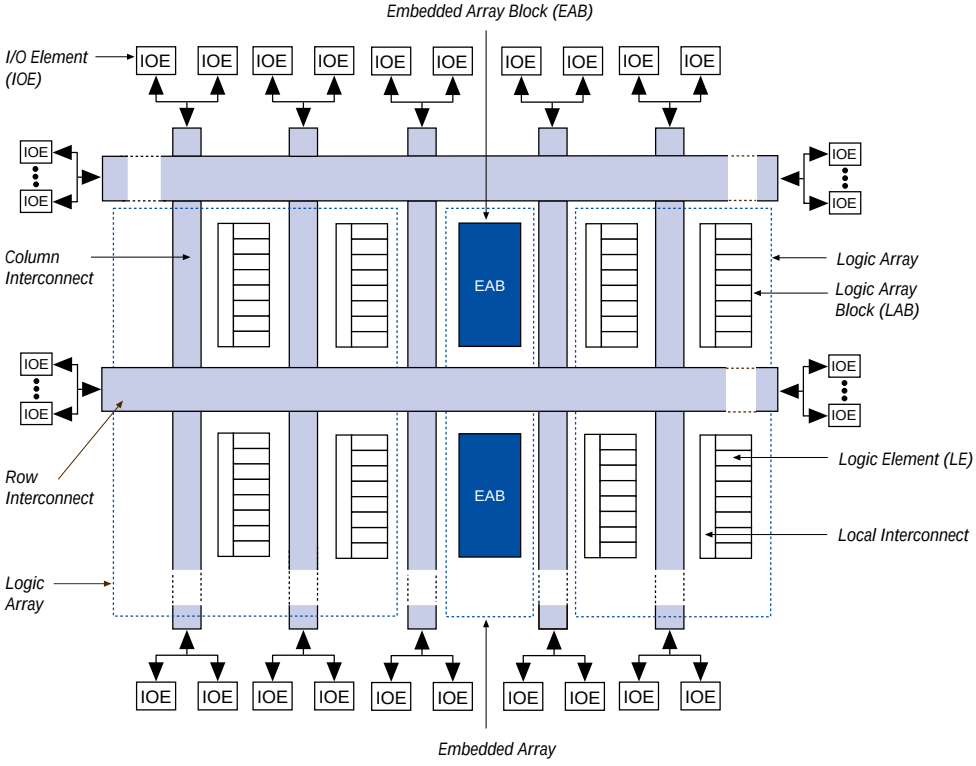
The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a four-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—such as 8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10KE devices (as well as to and from device pins) are provided by the FastTrack Interconnect routing structure, which is a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect routing structure. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 0.9 ns and hold times of 0 ns. As outputs, these registers provide clock-to-output times as low as 3.0 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

Figure 1 shows a block diagram of the FLEX 10KE architecture. Each group of LEs is combined into an LAB; groups of LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect routing structure. IOEs are located at the end of each row and column of the FastTrack Interconnect routing structure.

Figure 1. FLEX 10KE Device Block Diagram

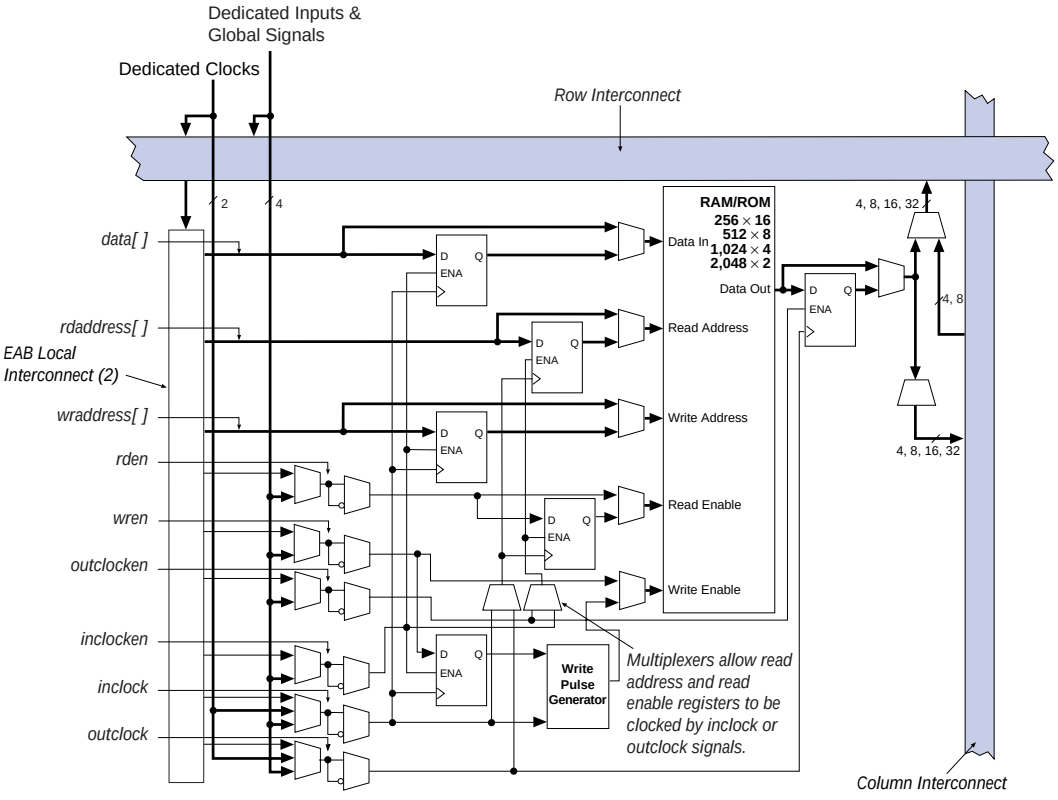


FLEX 10KE devices provide six dedicated inputs that drive the flipflops' control inputs and ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect routing structure. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

The EAB can also be used for bidirectional, dual-port memory applications where two ports read or write simultaneously. To implement this type of dual-port memory, two EABs are used to support two simultaneous read or writes.

Alternatively, one clock and clock enable can be used to control the input registers of the EAB, while a different clock and clock enable control the output registers (see Figure 2).

Figure 2. FLEX 10KE Device in Dual-Port RAM Mode *Notes (1)*



Notes:

(1) All registers can be asynchronously cleared by EAB local interconnect signals, global signals, or the chip-wide reset.

(2) EPF10K30E and EPF10K50E devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, and EPF10K200E devices have 104 EAB local interconnect channels.

FastTrack Interconnect Routing Structure

In the FLEX 10KE architecture, connections between LEs, EABs, and device I/O pins are provided by the FastTrack Interconnect routing structure, which is a series of continuous horizontal and vertical routing channels that traverses the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect routing structure consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the row. The column interconnect routes signals between rows and can drive I/O pins.

Row channels drive into the LAB or EAB local interconnect. The row signal is buffered at every LAB or EAB to reduce the effect of fan-out on delay. A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in a LAB drive the row interconnect.

Each column of LABs or EABs is served by a dedicated column interconnect. The column interconnect that serves the EABs has twice as many channels as other column interconnects. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs or EABs in the device. A signal from the column interconnect, which can be either the output of a LE or an input from an I/O pin, must be routed to the row interconnect before it can enter a LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, a LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This flexibility enables routing resources to be used more efficiently (see Figure 13).

When dedicated inputs drive non-inverted and inverted peripheral clears, clock enables, and output enables, two signals on the peripheral control bus will be used.

Tables 8 and 9 list the sources for each peripheral control signal, and show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals. The tables also show the rows that can drive global signals.

Table 8. Peripheral Bus Sources for EPF10K30E, EPF10K50E & EPF10K50S Devices

Peripheral Control Signal	EPF10K30E	EPF10K50E EPF10K50S
OE0	Row A	Row A
OE1	Row B	Row B
OE2	Row C	Row D
OE3	Row D	Row F
OE4	Row E	Row H
OE5	Row F	Row J
CLKENA0/CLK0/GLOBAL0	Row A	Row A
CLKENA1/OE6/GLOBAL1	Row B	Row C
CLKENA2/CLR0	Row C	Row E
CLKENA3/OE7/GLOBAL2	Row D	Row G
CLKENA4/CLR1	Row E	Row I
CLKENA5/CLK1/GLOBAL3	Row F	Row J

Table 9. Peripheral Bus Sources for EPF10K100E, EPF10K130E, EPF10K200E & EPF10K200S Devices

Peripheral Control Signal	EPF10K100E	EPF10K130E	EPF10K200E EPF10K200S
OE0	Row A	Row C	Row G
OE1	Row C	Row E	Row I
OE2	Row E	Row G	Row K
OE3	Row L	Row N	Row R
OE4	Row I	Row K	Row O
OE5	Row K	Row M	Row Q
CLKENA0/CLK0/GLOBAL0	Row F	Row H	Row L
CLKENA1/OE6/GLOBAL1	Row D	Row F	Row J
CLKENA2/CLR0	Row B	Row D	Row H
CLKENA3/OE7/GLOBAL2	Row H	Row J	Row N
CLKENA4/CLR1	Row J	Row L	Row P
CLKENA5/CLK1/GLOBAL3	Row G	Row I	Row M

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in Tables 8 and 9. An internally generated signal can drive a global signal, providing the same low-skew, low-delay characteristics as a signal driven by an input pin. An LE drives the global signal by driving a row line that drives the peripheral bus, which then drives the global signal. This feature is ideal for internally generated clear or clock signals with high fan-out. However, internally driven global signals offer no advantage over the general-purpose interconnect for routing data signals. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

The chip-wide output enable pin is an active-high pin (DEV_OE) that can be used to tri-state all pins on the device. This option can be set in the Altera software. On EPF10K50E and EPF10K200E devices, the built-in I/O pin pull-up resistors (which are active during configuration) are active when the chip-wide output enable pin is asserted. The registers in the IOE can also be reset by the chip-wide reset pin.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel (see Figure 16).

Figure 16. FLEX 10KE Row-to-IOE Connections

The values for m and n are provided in Table 10.

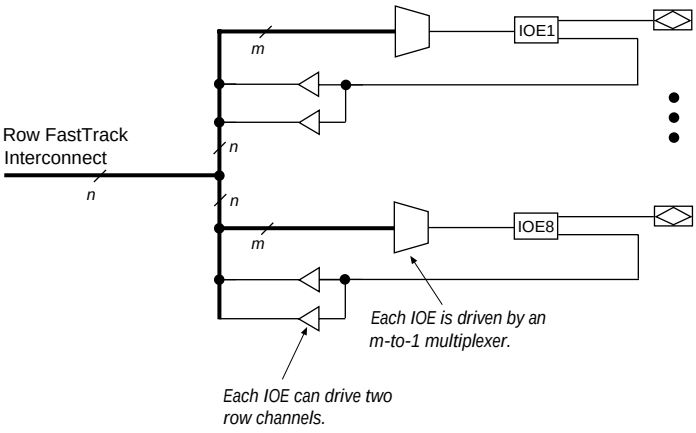


Table 10 lists the FLEX 10KE row-to-IOE interconnect resources.

Table 10. FLEX 10KE Row-to-IOE Interconnect Resources

Device	Channels per Row *(n)*	Row Channels per Pin *(m)*
EPF10K30E	216	27
EPF10K50E EPF10K50S	216	27
EPF10K100E	312	39
EPF10K130E	312	39
EPF10K200E EPF10K200S	312	39

Table 13. ClockLock & ClockBoost Parameters for -2 Speed-Grade Devices

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)		25		75	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)		16		37.5	MHz
f_{CLKDEV}	Input deviation from user specification in the MAX+PLUS II software *(1)*				25,000 *(2)*	PPM
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)				100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(3)*				10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(4)*	$t_{INCLKSTB}$ < 100			250	ps
		$t_{INCLKSTB}$ < 50			200 *(4)*	ps
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		40	50	60	%

Notes to tables:

(1) To implement the ClockLock and ClockBoost circuitry with the MAX+PLUS II software, designers must specify the input frequency. The Altera software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The f_{CLKDEV} parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.

(2) Twenty-five thousand parts per million (PPM) equates to 2.5% of input clock period.

(3) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration because the t_{LOCK} value is less than the time required for configuration.

(4) The t_{JITTER} specification is measured under long-term observation. The maximum value for t_{JITTER} is 200 ps if $t_{INCLKSTB}$ is lower than 50 ps.

I/O Configuration

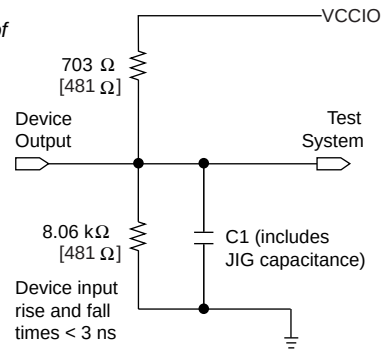
This section discusses the peripheral component interconnect (PCI) pull-up clamping diode option, slew-rate control, open-drain output option, and MultiVolt I/O interface for FLEX 10KE devices. The PCI pull-up clamping diode, slew-rate control, and open-drain output options are controlled pin-by-pin via Altera software logic options. The MultiVolt I/O interface is controlled by connecting V_{CCIO} to a different voltage than V_{CCINT}. Its effect can be simulated in the Altera software via the **Global Project Device Options** dialog box (Assign menu).

Generic Testing

Each FLEX 10KE device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10KE devices are made under conditions equivalent to those shown in Figure 21. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. FLEX 10KE AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V. devices or outputs.



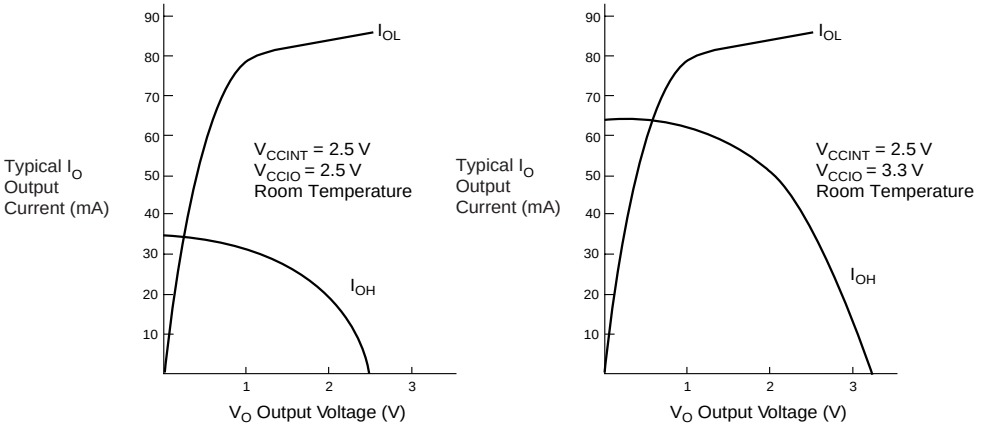
Operating Conditions

Tables 19 through 23 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V FLEX 10KE devices.

Table 19. FLEX 10KE 2.5-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, TQFP, BGA, and FineLine BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Figure 23. Output Drive Characteristics of FLEX 10KE Devices *Note (1)*



Note:
(1) These are transient (AC) currents.

Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (t_{CO})
- Interconnect delay ($t_{SAMEROW}$)
- LE look-up table delay (t_{LUT})
- LE register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Table 27. EAB Timing Macroparameters *Note (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 30. External Bidirectional Timing Parameters *Note (9)*		
Symbol	**Parameter**	**Conditions**
$t_{INSUBIDIR}$	Setup time for bi-directional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
t_{INH}	Hold time with global clock at IOE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	C1 = 35 pF
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate= off	C1 = 35 pF

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
(2) Operating conditions: VCCIO = 3.3 V ±10% for commercial or industrial use.
(3) Operating conditions: VCCIO = 2.5 V ±5% for commercial or industrial use in EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E, and EPF10K200S devices.
(4) Operating conditions: VCCIO = 3.3 V.
(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.
(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
(8) Contact Altera Applications for test circuit specifications and test conditions.
(9) This timing parameter is sample-tested only.
(10) This parameter is measured with the measurement and test conditions, including load, specified in the PCI Local Bus Specification, revision 2.2.

Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 34. EPF10K30E Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.4		7.6		8.8	ns
$t_{EABRCOMB}$	6.4		7.6		8.8		ns
$t_{EABRCREG}$	4.4		5.1		6.0		ns
t_{EABWP}	2.5		2.9		3.3		ns
$t_{EABWCOMB}$	6.0		7.0		8.0		ns
$t_{EABWCREG}$	6.8		7.8		9.0		ns
t_{EABDD}		5.7		6.7		7.7	ns
$t_{EABDATACO}$		0.8		0.9		1.1	ns
$t_{EABDATASU}$	1.5		1.7		2.0		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	1.3		1.4		1.7		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.5		1.7		2.0		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.3		ns
t_{EABWAH}	0.5		0.5		0.4		ns
t_{EABWO}		5.1		6.0		6.8	ns

Table 45. EPF10K100E Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.2	ns
t_{CASC}		0.6		0.9		1.2	ns
t_{C}		0.8		1.0		1.4	ns
t_{CO}		0.6		0.8		1.1	ns
t_{COMB}		0.4		0.5		0.7	ns
t_{SU}	0.4		0.6		0.7		ns
t_{H}	0.5		0.7		0.9		ns
t_{PRE}		0.8		1.0		1.4	ns
t_{CLR}		0.8		1.0		1.4	ns
t_{CH}	1.5		2.0		2.5		ns
t_{CL}	1.5		2.0		2.5		ns

Table 46. EPF10K100E Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.7		2.0		2.6	ns
t_{IOC}		0.0		0.0		0.0	ns
t_{IOCO}		1.4		1.6		2.1	ns
t_{IOCOMB}		0.5		0.7		0.9	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.7		0.9		1.2		ns
t_{IOCLR}		0.5		0.7		0.9	ns
t_{OD1}		3.0		4.2		5.6	ns
t_{OD2}		3.0		4.2		5.6	ns
t_{OD3}		4.0		5.5		7.3	ns
t_{XZ}		3.5		4.6		6.1	ns
t_{ZX1}		3.5		4.6		6.1	ns
t_{ZX2}		3.5		4.6		6.1	ns
t_{ZX3}		4.5		5.9		7.8	ns
t_{INREG}		2.0		2.6		3.5	ns
t_{IOFD}		0.5		0.8		1.2	ns
t_{INCOMB}		0.5		0.8		1.2	ns

Table 48. EPF10K100E Device EAB Internal Timing Macroparameters *(Part 2 of 2)* *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	5.9		7.7		10.3		ns
$t_{EABWCREG}$	5.4		7.0		9.4		ns
t_{EABDD}		3.4		4.5		5.9	ns
$t_{EABDATACO}$		0.5		0.7		0.8	ns
$t_{EABDATASU}$	0.8		1.0		1.4		ns
$t_{EABDATAH}$	0.1		0.1		0.2		ns
$t_{EABWESU}$	1.1		1.4		1.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.0		1.3		1.7		ns
t_{EABWDH}	0.2		0.2		0.3		ns
$t_{EABWASU}$	4.1		5.2		6.8		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		3.4		4.5		5.9	ns

Table 49. EPF10K100E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.1		3.6		4.4	ns
t_{DIN2LE}		0.3		0.4		0.5	ns
$t_{DIN2DATA}$		1.6		1.8		2.0	ns
$t_{DCLK2IOE}$		0.8		1.1		1.4	ns
$t_{DCLK2LE}$		0.3		0.4		0.5	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		1.5		2.5		3.4	ns
$t_{SAMECOLUMN}$		0.4		1.0		1.6	ns
$t_{DIFFROW}$		1.9		3.5		5.0	ns
$t_{TWOROWS}$		3.4		6.0		8.4	ns
$t_{LEPERIPH}$		4.3		5.4		6.5	ns
$t_{LABCARRY}$		0.5		0.7		0.9	ns
$t_{LABCASC}$		0.8		1.0		1.4	ns

Table 62. EPF10K200E Device EAB Internal Timing Macroparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABWCOMB}$	6.7		8.1		10.7		ns
$t_{EABWCREG}$	6.6		8.0		10.6		ns
t_{EABDD}		4.0		5.1		6.7	ns
$t_{EABDATACO}$		0.8		1.0		1.3	ns
$t_{EABDATASU}$	1.3		1.6		2.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	0.9		1.1		1.5		ns
t_{EABWEH}	0.4		0.5		0.6		ns
$t_{EABWDSU}$	1.5		1.8		2.4		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.7		ns
t_{EABWAH}	0.4		0.5		0.7		ns
t_{EABWO}		3.4		4.4		5.8	ns

Table 63. EPF10K200E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		4.6		5.7	ns
t_{DIN2LE}		1.7		1.7		2.0	ns
$t_{DIN2DATA}$		1.9		2.1		3.0	ns
$t_{DCLK2IOE}$		2.5		2.9		4.0	ns
$t_{DCLK2LE}$		1.7		1.7		2.0	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.6		3.6	ns
$t_{SAMECOLUMN}$		2.5		2.7		4.1	ns
$t_{DIFFROW}$		4.8		5.3		7.7	ns
$t_{TWOROWS}$		7.1		7.9		11.3	ns
$t_{LEPERIPH}$		7.0		7.6		9.0	ns
$t_{LABCARRY}$		0.1		0.1		0.2	ns
$t_{LABCASC}$		0.9		1.0		1.4	ns

Table 66. EPF10K50S Device LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CGENR}		0.1		0.1		0.1	ns
t_{CASC}		0.5		0.8		1.0	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.6		0.6		0.7	ns
t_{COMB}		0.3		0.4		0.5	ns
t_{SU}	0.5		0.6		0.7		ns
t_{H}	0.5		0.6		0.8		ns
t_{PRE}		0.4		0.5		0.7	ns
t_{CLR}		0.8		1.0		1.2	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns

Table 67. EPF10K50S Device IOE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		1.3		1.3		1.9	ns
t_{IOC}		0.3		0.4		0.4	ns
t_{IOCO}		1.7		2.1		2.6	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	0.8		1.0		1.3		ns
t_{IOH}	0.4		0.5		0.6		ns
t_{IOCLR}		0.2		0.2		0.4	ns
t_{OD1}		1.2		1.2		1.9	ns
t_{OD2}		0.7		0.8		1.7	ns
t_{OD3}		2.7		3.0		4.3	ns
t_{XZ}		4.7		5.7		7.5	ns
t_{ZX1}		4.7		5.7		7.5	ns
t_{ZX2}		4.2		5.3		7.3	ns
t_{ZX3}		6.2		7.5		9.9	ns
t_{INREG}		3.5		4.2		5.6	ns
t_{IOFD}		1.1		1.3		1.8	ns
t_{INCOMB}		1.1		1.3		1.8	ns